



AMENDMENTS TO THE CLAIMS:

Please cancel claims 1 and 9, without prejudice. Kindly amend claims 2, 3 and 10, and add new claims 14 and 15, as shown below.

This listing of claims will replace all prior versions and listings of claims in the Application.

Claim 1 (canceled)

Claim 2 (currently amended): ~~The semiconductor device according to claim 1, further comprising:~~ A semiconductor device comprising:

a first substrate;

a first heatsink plate connected to said first substrate;

a second substrate having main and rear surfaces, said rear surface of said second substrate being connected to said first heatsink plate;

a semiconductor chip having a main surface bonded to said main surface of said second substrate;

a second heatsink plate connected to a rear surface of said semiconductor chip;

a first pad coupled to a rear surface of said first substrate; and

a second pad coupled to said main surface of said second substrate to be electrically connected to said semiconductor chip,

wherein said first substrate includes a first interconnection therethrough connected to said first pad,

wherein said second substrate includes a second interconnection therethrough connected to said second pad, and

wherein said first heatsink plate includes a via contact providing an electrical connection between said first and second interconnections.

Claim 3 (currently amended): The semiconductor device according to claim [[1]] 2, wherein said first heatsink plate includes:

a body portion disposed between said first and second substrates;

a side portion connected to said body portion to form an edge therebetween.

Claim 4 (original): The semiconductor device according to claim 3, wherein said side portion is perpendicular to said body portion.

Claim 5 (original): The semiconductor device according to claim 3, wherein said first heatsink plate further includes an upper portion connected to said side portion.

Claim 6 (original): The semiconductor device according to claim 5, wherein said upper portion is perpendicular to said side portion.

Claim 7 (original): The semiconductor device according to claim 5, wherein said second heatsink plate is connected to said upper portion.

Claim 8 (original): The semiconductor device according to claim 2, wherein said first and second heatsink plate are connected to each other to form an enclosure around said semiconductor chip.

Claim 9 (canceled)

Claim 10 (currently amended): ~~The method according to claim 9, further comprising: A~~
fabrication method of a semiconductor device comprising:

coupling a rear surface of a first heatsink plate to a main surface of a first substrate;

coupling a rear surface of a second substrate to a main surface of said first heatsink

plate;

flipchip bonding a semiconductor chip onto said main surface of said second substrate;

coupling a second heatsink plate to a rear surface of said semiconductor chip;

folding said first heatsink plate on an edge to form body and side portions within said first heatsink plate, said body portion being disposed between said first and second substrates.

Claim 11 (original): The method according to claim 10, further comprising:

folding said first heatsink plate on another edge to form upper portions connected to said side portions within said first heatsink plate.

Claim 12 (original): The method according to claim 11, further comprising:

coupling said second heatsink plate to said upper portions.

Claim 13 (original): The method according to claim 12, wherein said first and second heatsink plates form an enclosure around said semiconductor chip.

Claim 14 (new): A semiconductor device comprising:

a first substrate;

a first heatsink plate connected to said first substrate;

a second substrate having main and rear surfaces, said rear surface of said second substrate being connected to said first heatsink plate;

a semiconductor chip having a main surface bonded to said main surface of said second substrate;

a second heatsink plate connected to a rear surface of said semiconductor chip without an insulating substrate of highly thermally conductive material.

Claim 15 (new): The semiconductor device according to claim 14, wherein said first heatsink

plate includes:

a body portion disposed between said first and second substrates;

a side portion connected to said body portion to form an edge therebetween.

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